

# Plasmonics and Nanoantennas for Infrared Detectors



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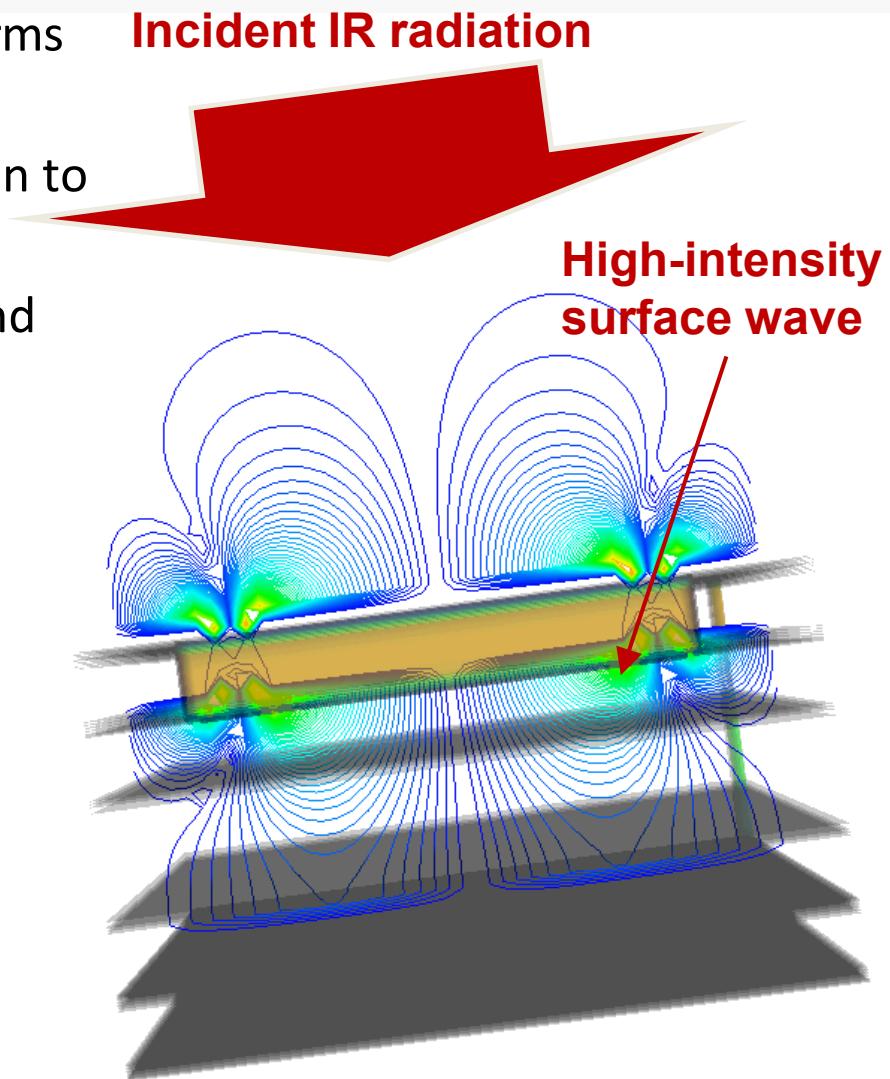
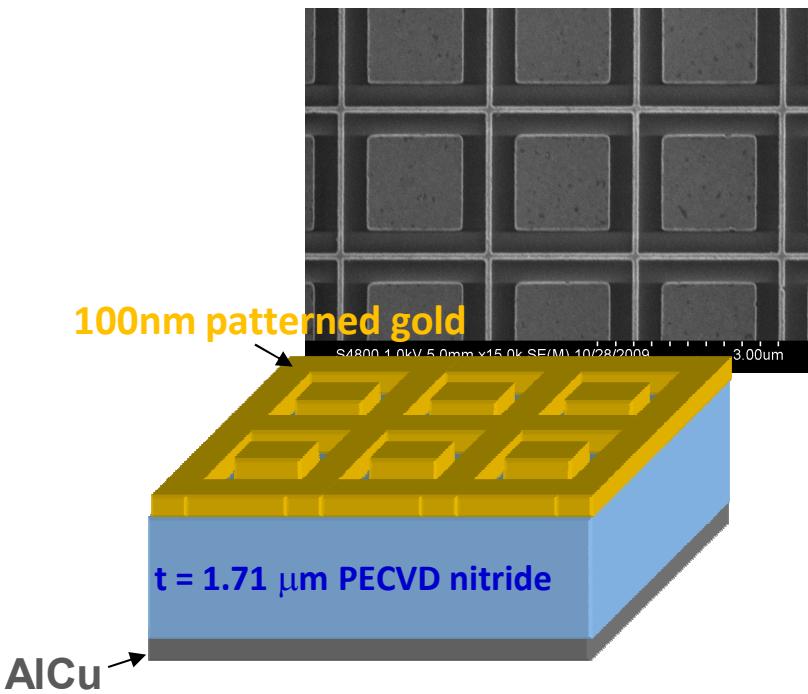


# Outline

- “Perfect Absorbers” and their application
- Application of nanoantenna concept to active devices
- Advantages over traditional detectors
- Our fabrication
- Results

# Nanoantennas as Perfect Absorbers

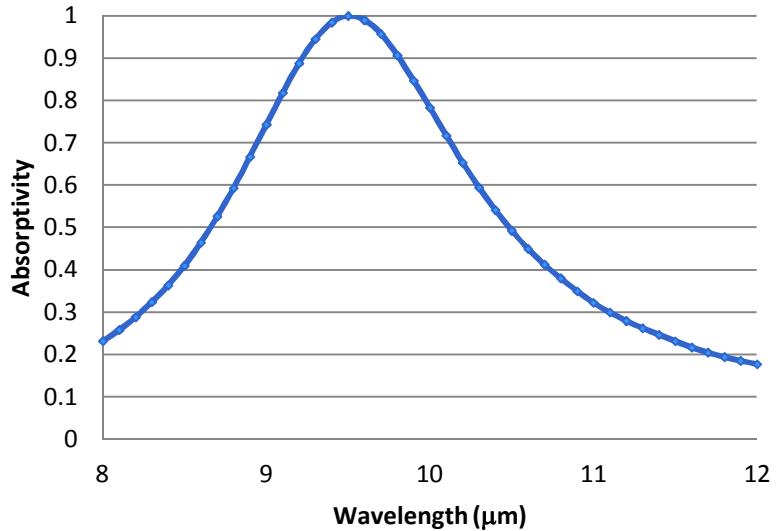
- Plasmons are electromagnetic waveforms with high field concentrations.
- Nanoantennas couple incident radiation to plasmons with near 100% efficiency.
- We have used this efficient coupling and field concentration to form “perfect absorbers” in the thermal infrared.



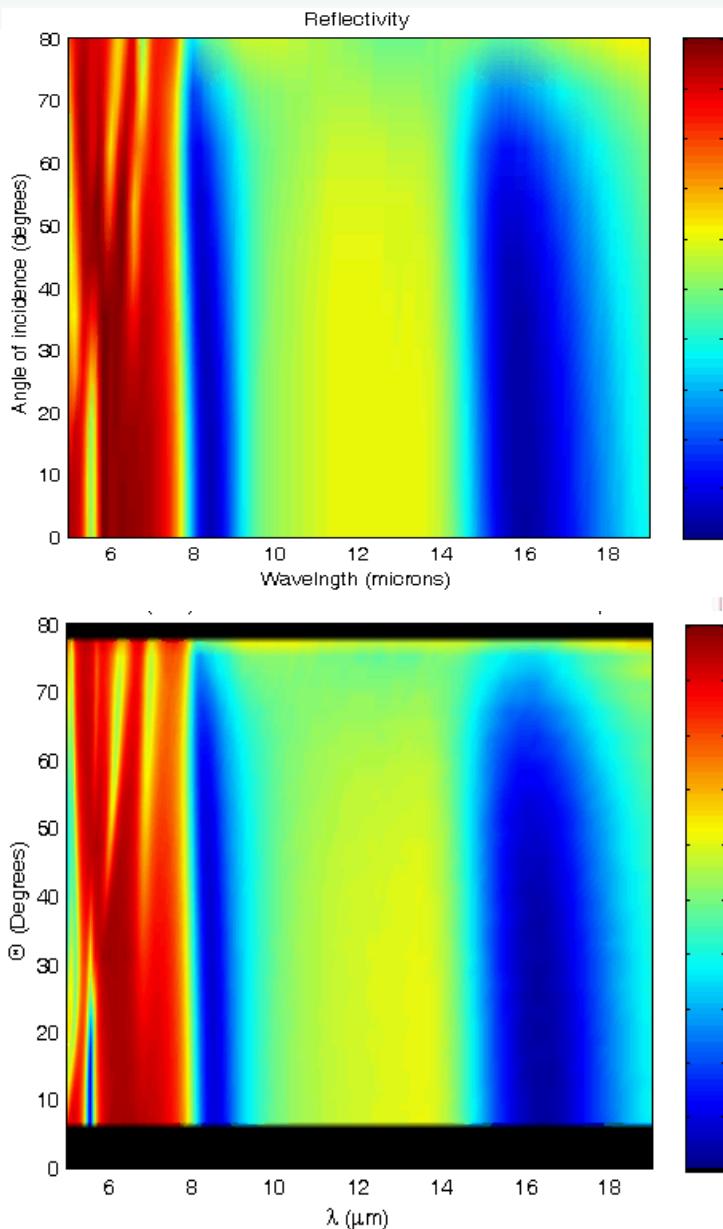
# Nanoantennas as Perfect Absorbers

- **Absorption bandwidth is determined by the parameters of the nanoantenna and the materials used.**

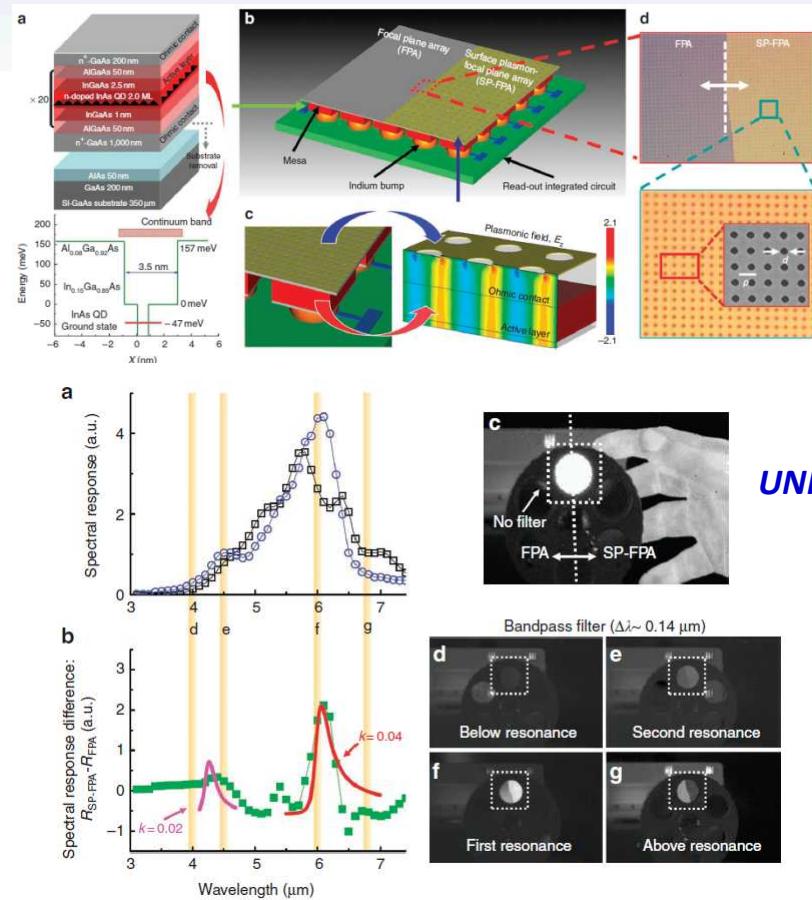
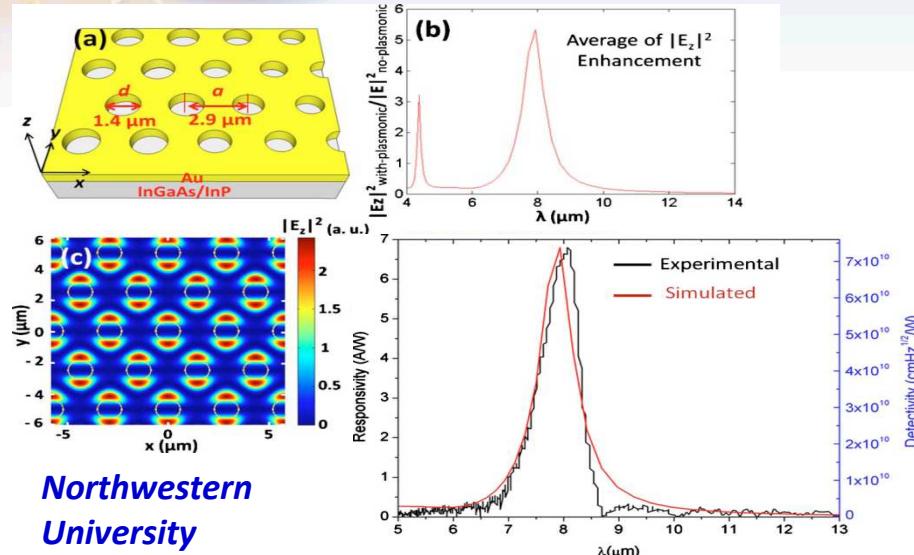
Absorption in Non-Dispersive Medium



- **We have excellent agreement between simulation and measurement. → great confidence in our models.**



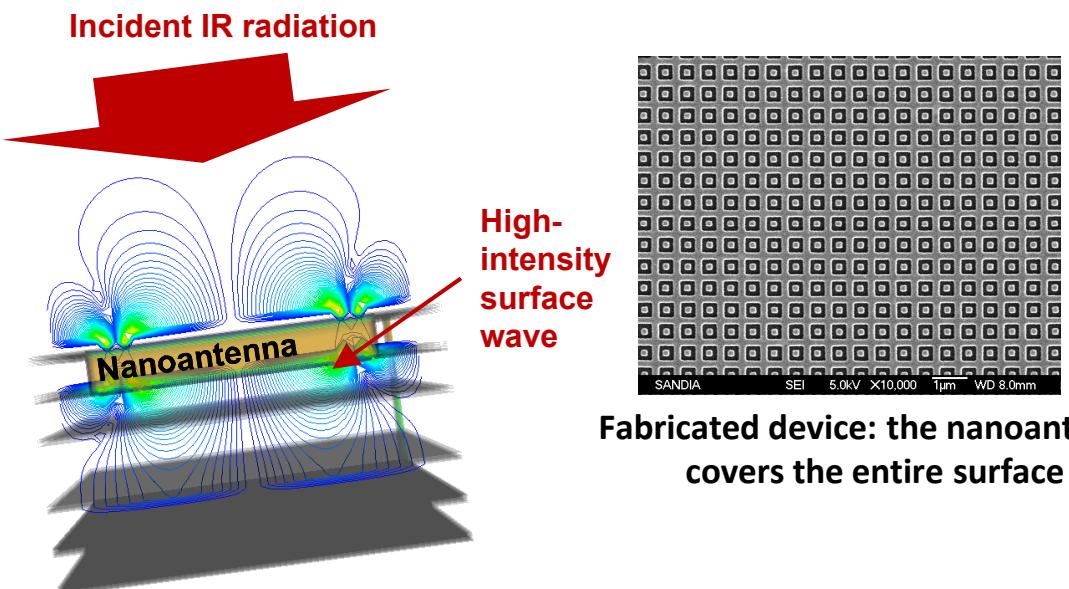
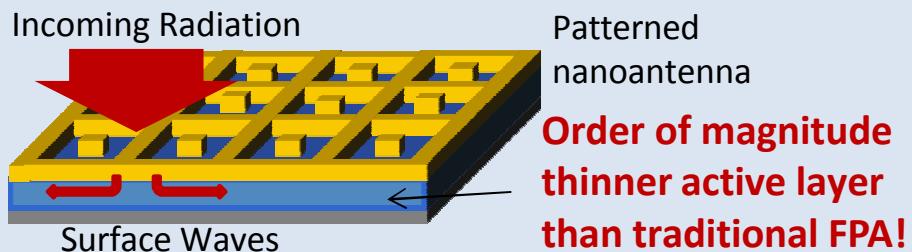
# Related Work



# Nanoantenna-Enhanced Infrared Detection

A method to improve all detector platforms by changing the way the energy interacts with the detecting layer.

Use nanoantenna to convert to tightly confined surface waves. → You only need active material where there is energy.



The concentration of the incident energy in the layer under the nanoantenna allows us to greatly modify existing detectors and envision new devices.

We are applying nanoantennas to

- III-V MWIR detectors
- bilayer graphene LWIR detectors
- germanium SWIR detectors.

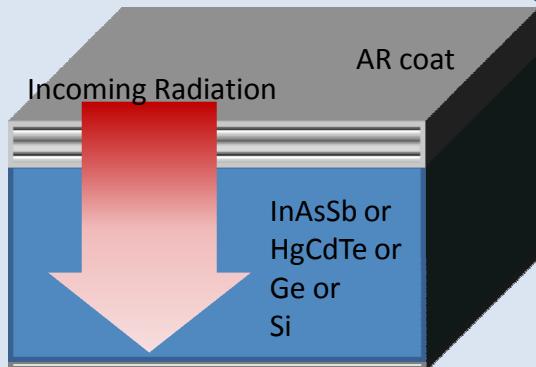
# Nanoantenna-Enhanced Infrared FPA

A method to improve all detector platforms by changing the way the energy interacts with the detecting layer.

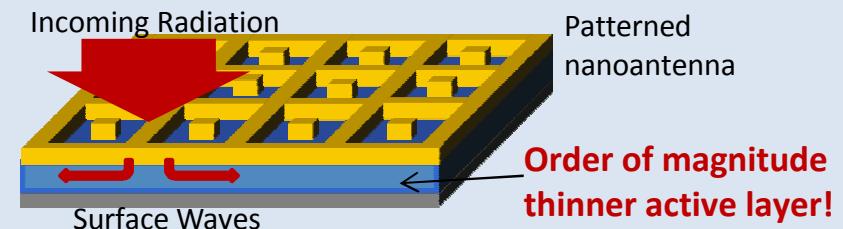
## Traditional FPA Pixel:

Active layer must be thick enough to absorb incoming radiation.

Thick active layer leads to dark current and crosstalk.



Our pixel: Use nanoantenna to convert to tightly confined surface waves. → You only need active material where there is energy.



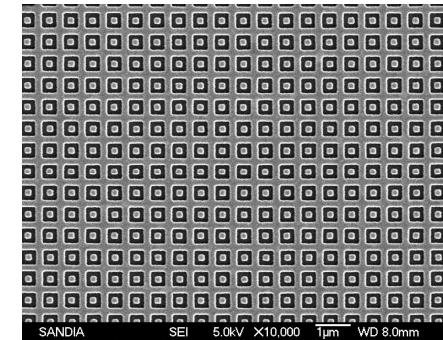
Very thin active layer leads to

- Less dark current
- Less crosstalk
- Faster operation

The nanoantenna gives us

- Spectral or polarization filtering by changing pattern from pixel to pixel
- Built-in wide-angle antireflection coating
- Built in EMI protection
- A material-agnostic device

We are currently applying nanoantennas to nBn, QWIP, Ge, and bilayer graphene detectors.



Fabricated device

# Replacement of a Thick Absorber Layer with a Nanoantenna-Enabled Thin Absorber

The nanoantenna solves both issues:

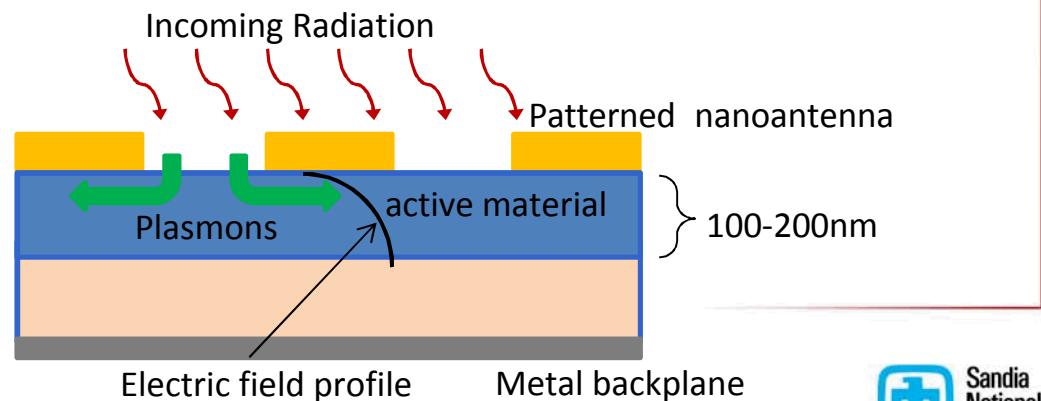
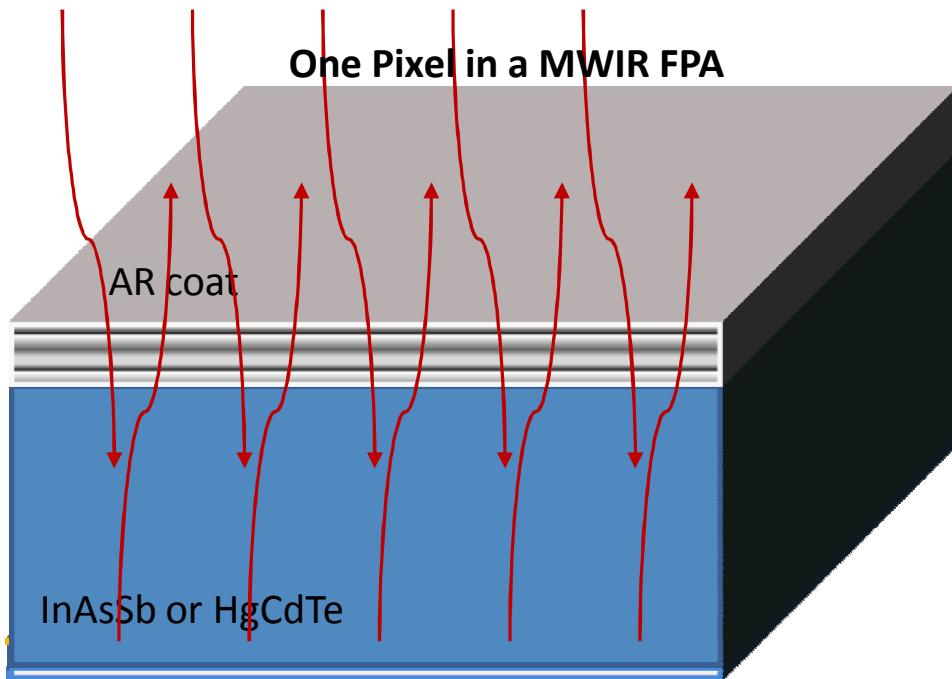
1. Lower the dark current (higher It couples incoming radiation to plasmon with no reflection) the material absorption. You need at least enough material so only the thin part of the light.

2. Strain material more; higher cutoff
3. Obtain higher yields.

Since these materials tend to be high index, you need an AR coat

But a thinner layer would not let us absorb the incident radiation efficiently.

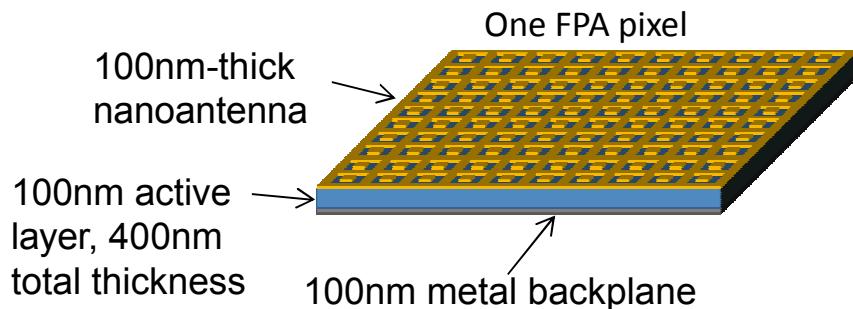
No AR coat would lead to much reflection.



# Advantages of a Thinner Active Layer

Integrate subwavelength nanoantenna with active material (MCT or InGaSb) for high-performance FPA.

InGaAsSb photodetectors are made at Sandia.



## What does thin buy you?



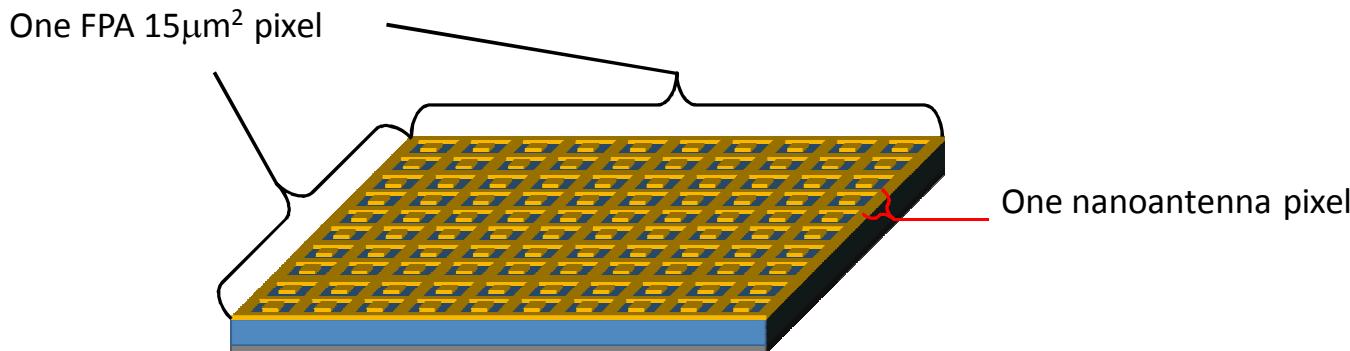
Volume of active material (MCT or nBn) required goes down by over an order of magnitude.

**Less material → lower dark current → better performance at a fixed temperature or equal performance at a higher temperature (less cooling required).**

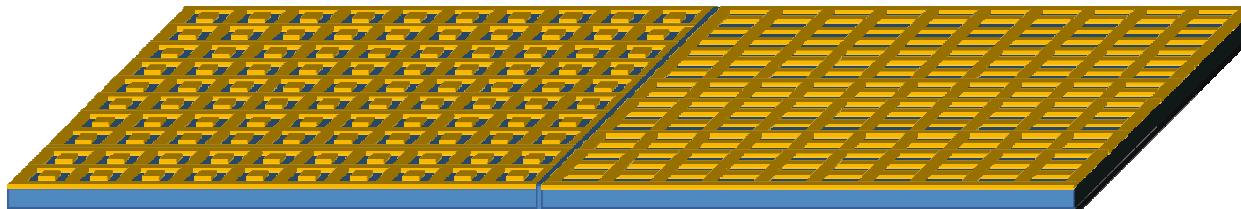
- Thin layer allows more freedom with strain of the material. In the case of nBn, we can push the cutoff wavelength higher by tenths of microns.
- Less material deposition = easier fab/higher yield/fewer dead pixels. Should lead to lower cost detectors.

# Advantages of the Nanoantenna Structure

- Top and bottom contacts allow direct connection.
- Filtering can be changed from FPA pixel-to-pixel simply by changing the antenna pattern (Spectral or polarization). This is difficult to do with thin films.
- Small antenna unit cell allows multiple unit cells per FPA pixel (for broadband).



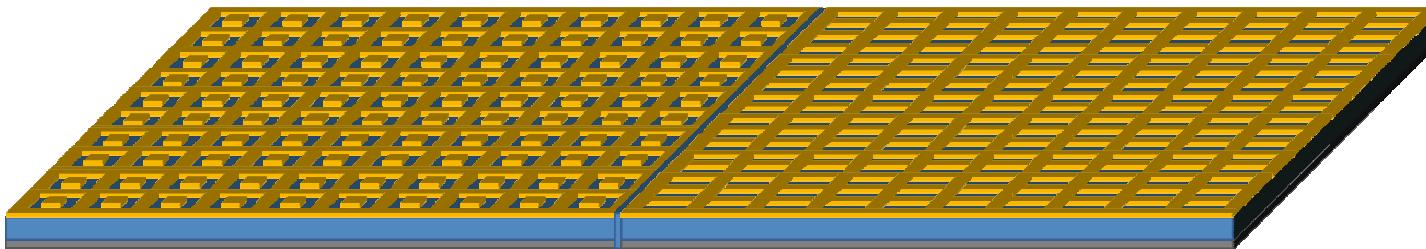
Two adjacent FPA pixels with different functionality.





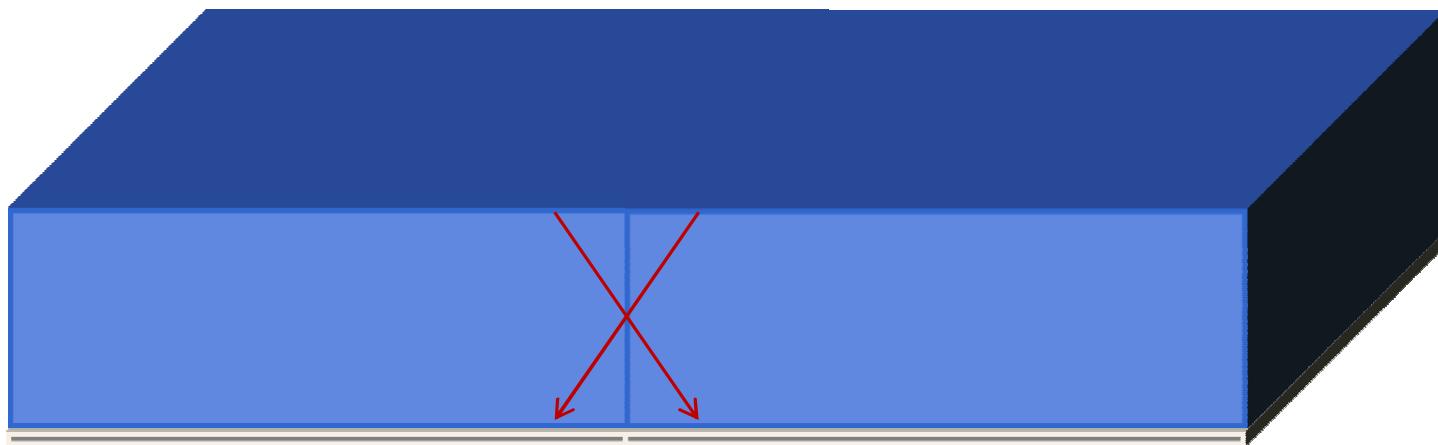
# Maximizing Active Area

Nanoantenna  
Enabled



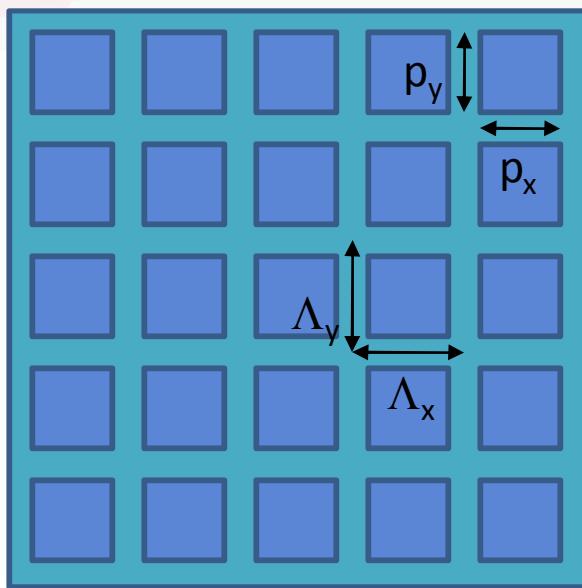
Thin absorber layer means that isolating adjacent pixels does not require the same area.

Traditional

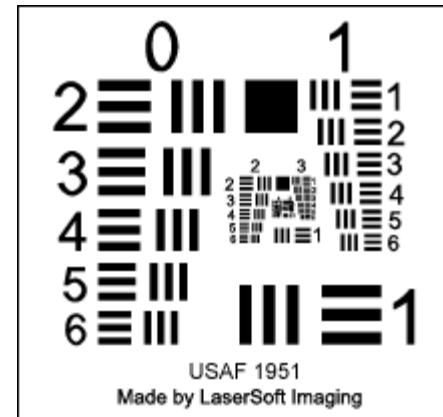


Traditional design requires more dead area between pixels to avoid crosstalk.

# Maximizing Active Area Improves MTF



$M \times N$  pixels



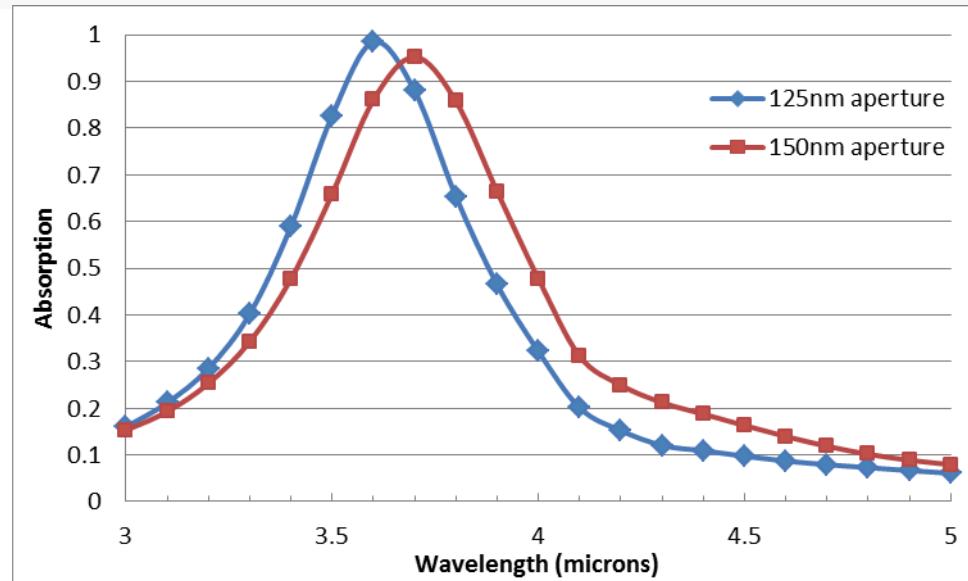
$$MTF(f_x, f_y) = [\text{sinc}((M \cdot \Lambda_x) \cdot f_x, (N \cdot \Lambda_y) \cdot f_y) * \text{comb}(\Lambda_x \cdot f_x, \Lambda_y \cdot f_y)] \cdot \text{sinc}(p_x \cdot f_x, p_y \cdot f_y)$$

Ideally for the mathematical MTF function, we want  $\Lambda_x$ ,  $\Lambda_y$  and  $p_x$ ,  $p_y$  as small as possible to maximize the MTF.

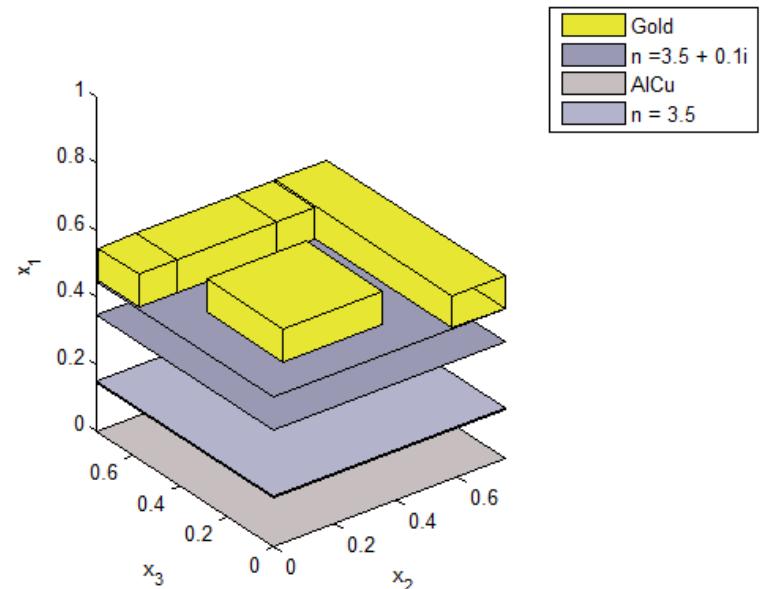
This is clearly impossible, but we can make  $\Lambda_x$  and  $\Lambda_y$  as small as possible for a given  $p_x$  and  $p_y$ .

# Optical Design of Nanoantenna

RCWA used to optimize the lateral parameters and layer thicknesses for a desired wavelength and maximum absorption.



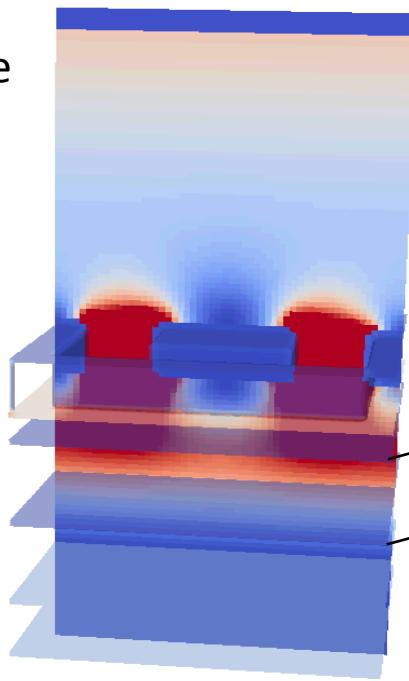
Peak of absorption curve is in the  $3.5\mu\text{m}$  to  $4.0\mu\text{m}$  range: middle of the absorption band for the active material we will be using.



# Optical Fields and Absorption

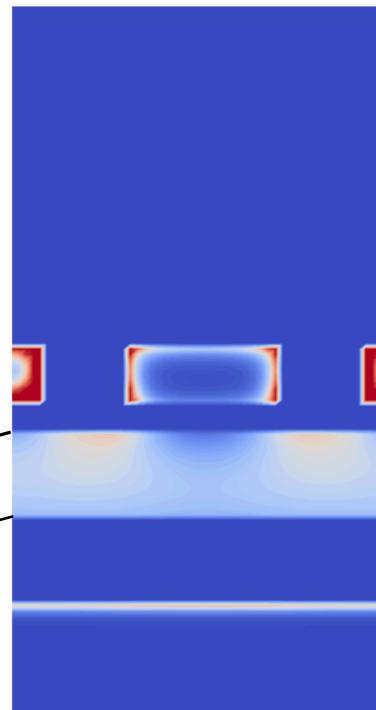
## Electric Field Magnitude

Incident plane wave



## Absorption

Metal Nanoantenna



Metal Nanoantenna

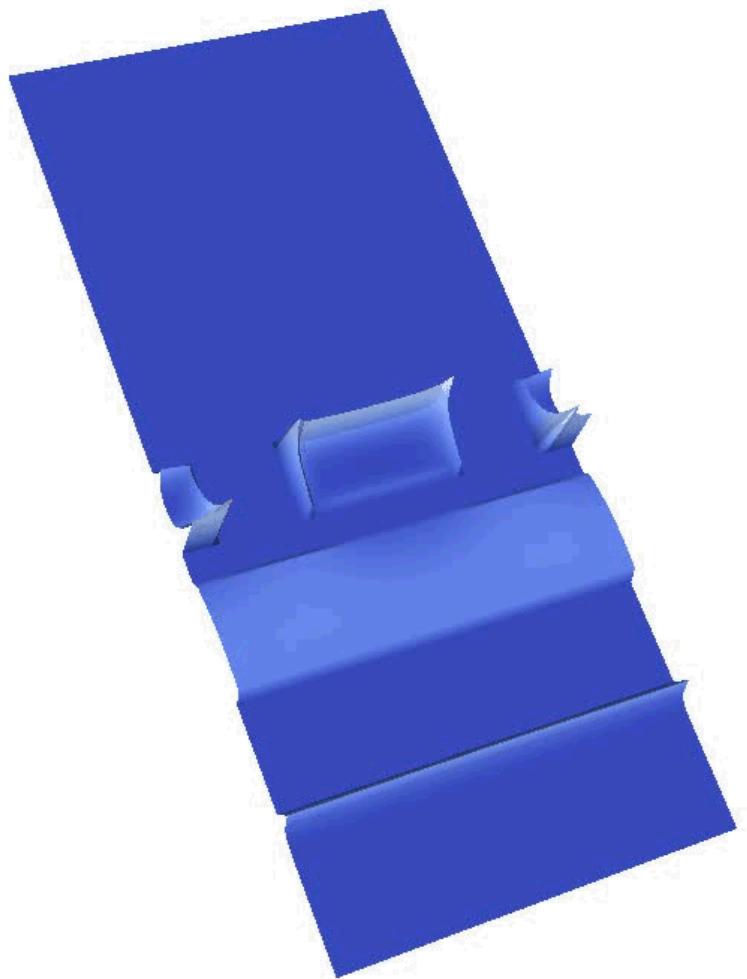
Absorbing layer

High electric fields generated around the nanoantenna; order of magnitude stronger than plane wave, concentrated in a couple hundred nanometers of surface.

Absorption at edge of metal and throughout active layer.



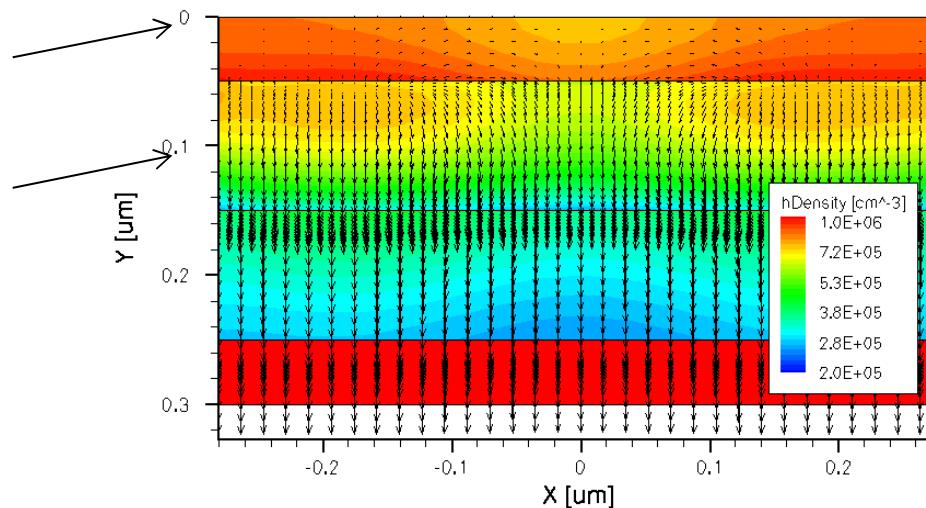
# Absorption as Function of Wavelength



# Electrical Modeling

Bottom of nanoantenna metal

Active layer



**Shows flow of carriers and if there is recombination at surfaces.**

**Useful to optimize the design of the epi stack.**

**Led to incorporation of buffer layer.**



## Fabrication

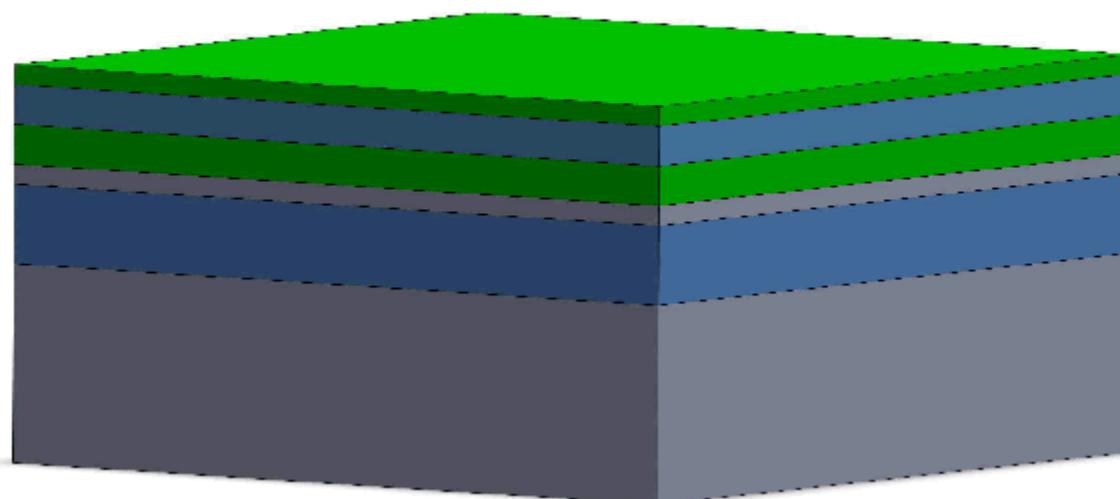
Not only is the active layer thinner than in a traditional detector, but it is sandwiched between the patterned metal nanoantenna and a metal backplane. This requires the development of a new process flow. I'll describe one of the ones that we have developed.

# Fabrication Process Flow

An example of a growth stack on a GaAsb substrate that includes:

- 50nm AlGa<sub>0.15</sub>AsSb absorber passivation layer
- 100nm InAsSb absorber
- 100nm AlGa<sub>0.15</sub>AsSb electron barrier
- 50nm p-type GaSb contact layer
- 100nm InAsSb etch stop layer

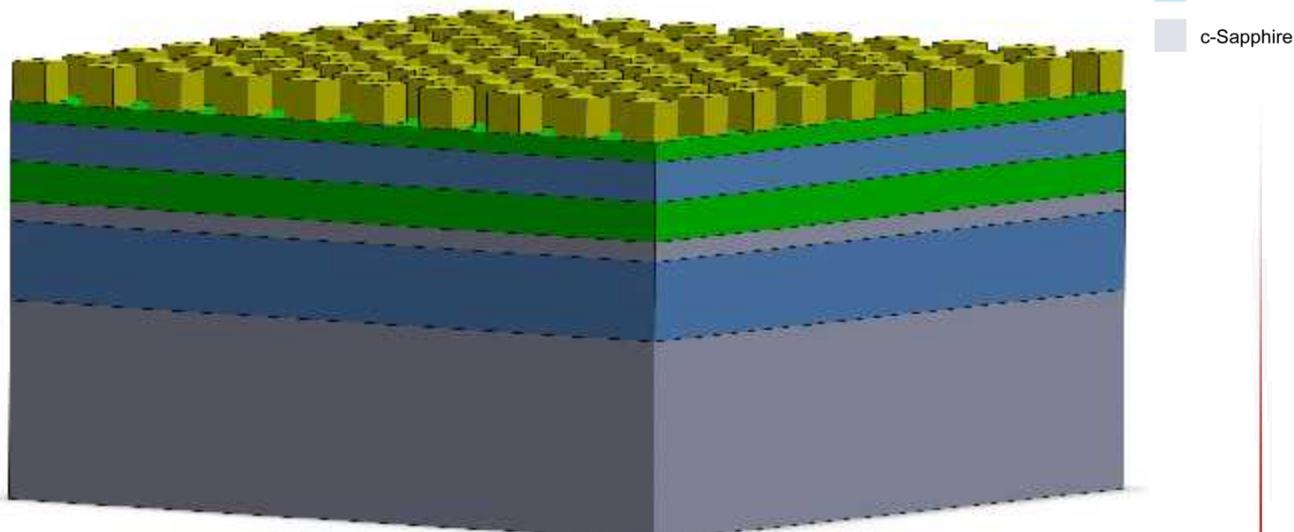
	GaSb
	InAsSb
	AlGaAsSb
	Au
	Ti
	Si <sub>3</sub> N <sub>4</sub>
	BCB
	c-Sapphire



# Fabrication Process Flow

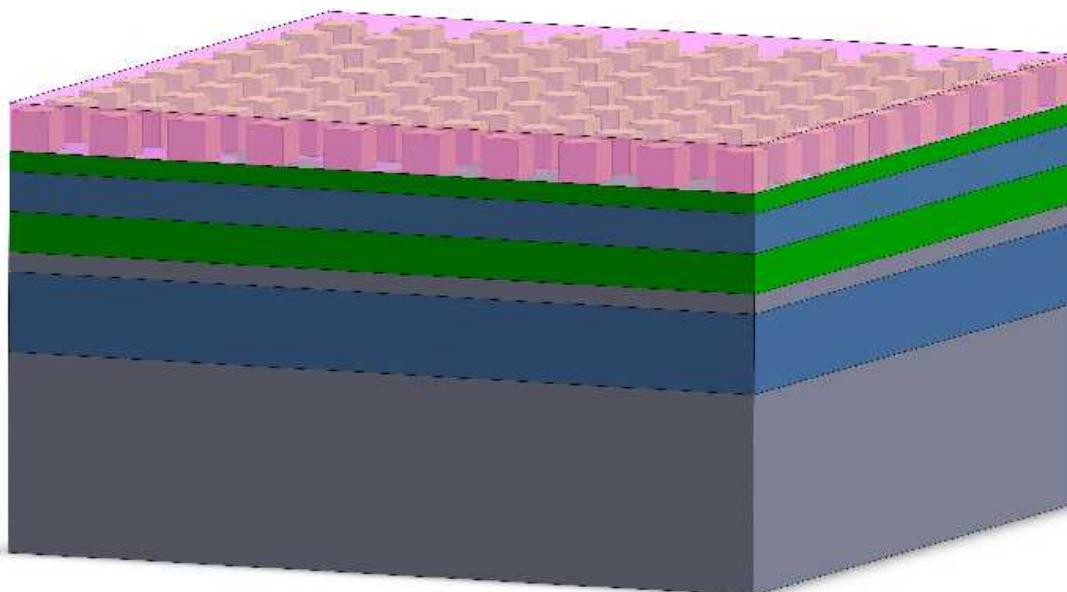
Nanoantenna (NA) fabrication is done on the absorber passivation layer using e-beam lithography.

The antenna is 100nm thick gold.



# Fabrication Process Flow

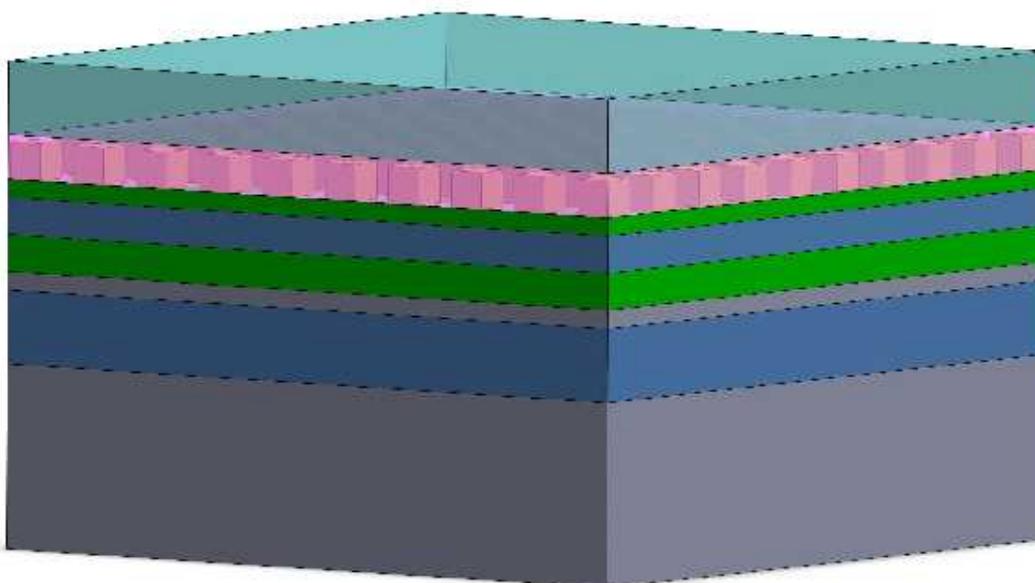
The NA is encapsulated with 300nm of  $\text{Si}_3\text{N}_4$ . The nitride provides a well-defined environment surrounding the antenna, in addition to providing an adhesion layer for the BCB.



<span style="background-color: #696969; border: 1px solid black; display: inline-block; width: 15px; height: 15px;"></span>	GaSb
<span style="background-color: #1E7EAD; border: 1px solid black; display: inline-block; width: 15px; height: 15px;"></span>	InAsSb
<span style="background-color: #00AEEF; border: 1px solid black; display: inline-block; width: 15px; height: 15px;"></span>	AlGaAsSb
<span style="background-color: #FFD700; border: 1px solid black; display: inline-block; width: 15px; height: 15px;"></span>	Au
<span style="border: 1px solid black; display: inline-block; width: 15px; height: 15px;"></span>	Ti
<span style="background-color: #F08080; border: 1px solid black; display: inline-block; width: 15px; height: 15px;"></span>	$\text{Si}_3\text{N}_4$
<span style="background-color: #AEC6E4; border: 1px solid black; display: inline-block; width: 15px; height: 15px;"></span>	BCB
<span style="background-color: #BDBDBD; border: 1px solid black; display: inline-block; width: 15px; height: 15px;"></span>	c-Sapphire

# Fabrication Process Flow

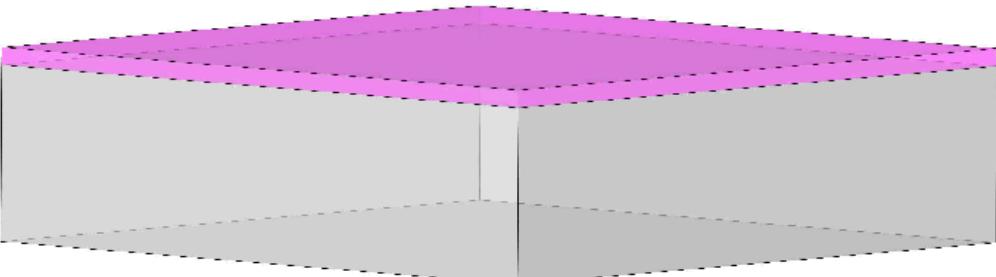
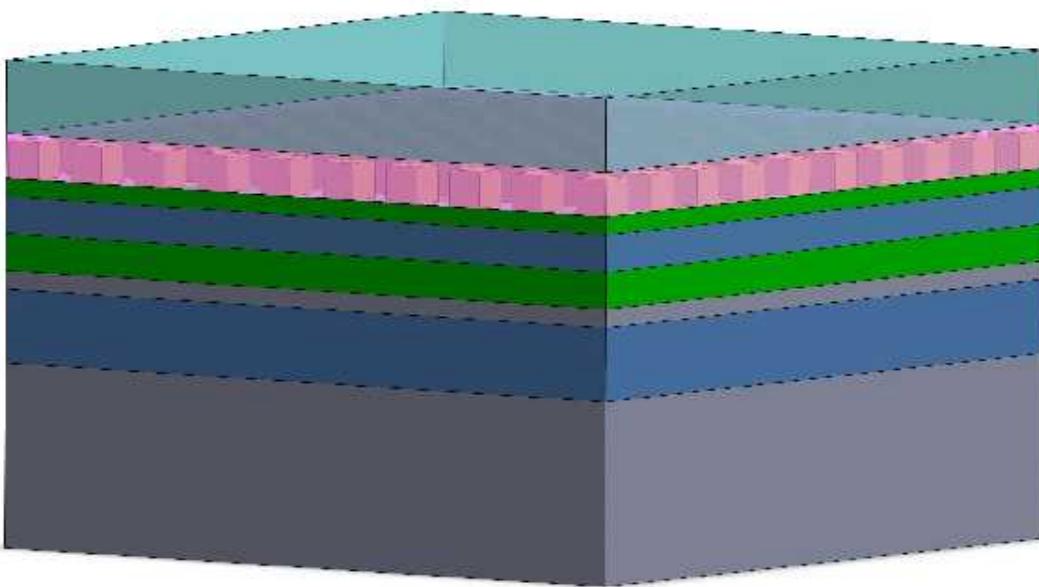
BCB is spin coated onto the nitride.



<span style="background-color: #555; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	GaSb
<span style="background-color: #005599; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	InAsSb
<span style="background-color: #008000; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	AlGaAsSb
<span style="background-color: #FFD700; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	Au
<span style="border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	Ti
<span style="background-color: #FF0000; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	$\text{Si}_3\text{N}_4$
<span style="background-color: #80C0FF; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	BCB
<span style="background-color: #B0B0B0; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	c-Sapphire

# Fabrication Process Flow

A coating of 100nm of  $\text{Si}_3\text{N}_4$  is deposited onto a c-sapphire handle piece to promote BCB adhesion.

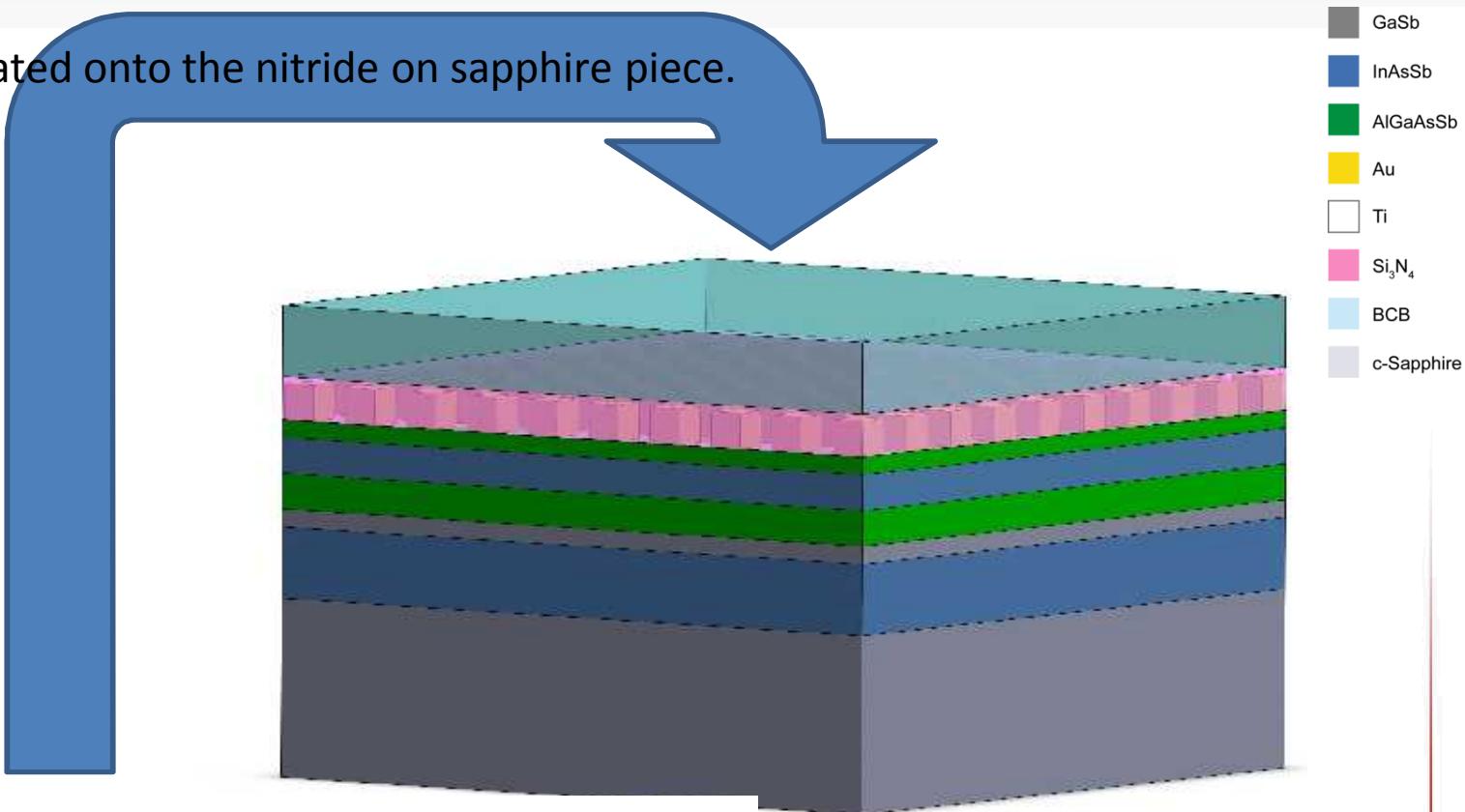
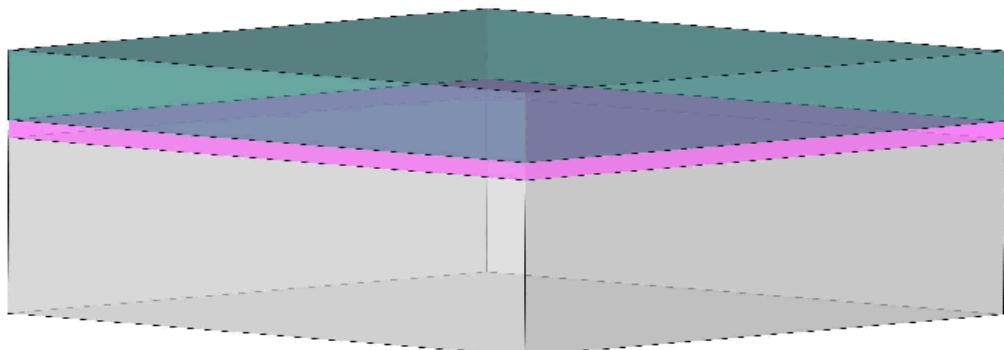


<span style="background-color: #666; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	GaSb
<span style="background-color: #005599; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	InAsSb
<span style="background-color: #008000; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	AlGaAsSb
<span style="background-color: #FFD700; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	Au
<span style="border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	Ti
<span style="background-color: #FF0000; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	$\text{Si}_3\text{N}_4$
<span style="background-color: #80C0FF; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	BCB
<span style="background-color: #B0B0B0; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	c-Sapphire

# Fabrication Process Flow

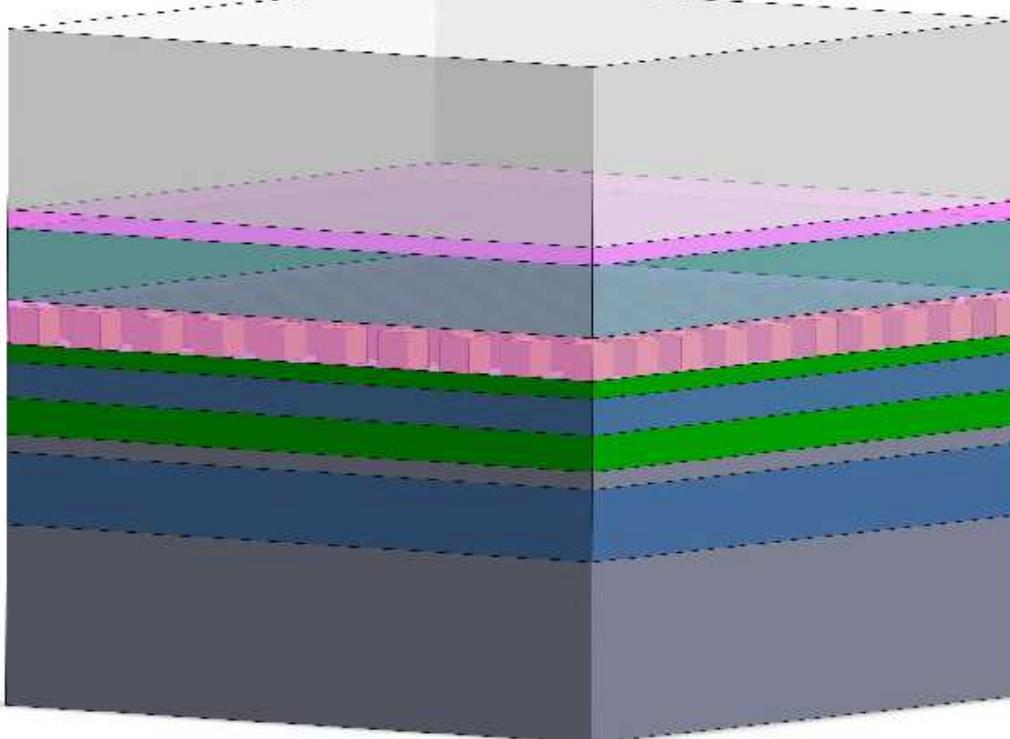
BCB is spin coated onto the nitride on sapphire piece.

Sapphire wafer  
is flipped and  
bonded.



# Fabrication Process Flow

The NA sample and the handle piece are then heated to 170°C, past the glass transition point of the BCB. The two pieces are then pressed together into intimate contact and slowly cooled to room temperature.

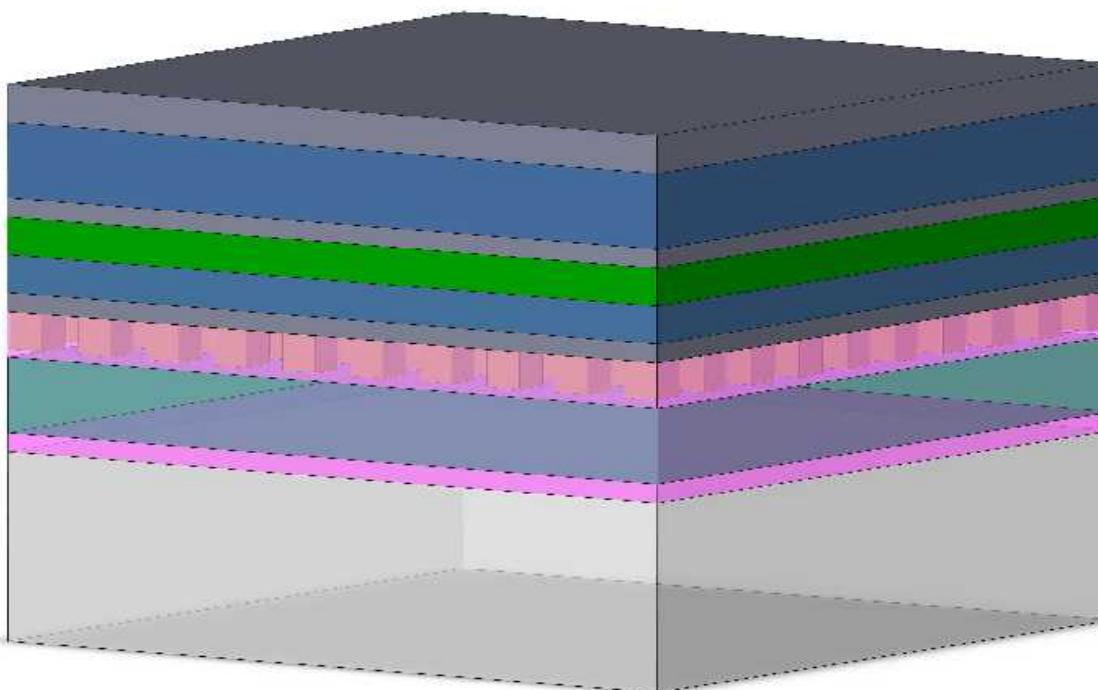


	GaSb
	InAsSb
	AlGaAsSb
	Au
	Ti
	Si <sub>3</sub> N <sub>4</sub>
	BCB
	c-Sapphire

# Fabrication Process Flow

Figure now flipped.

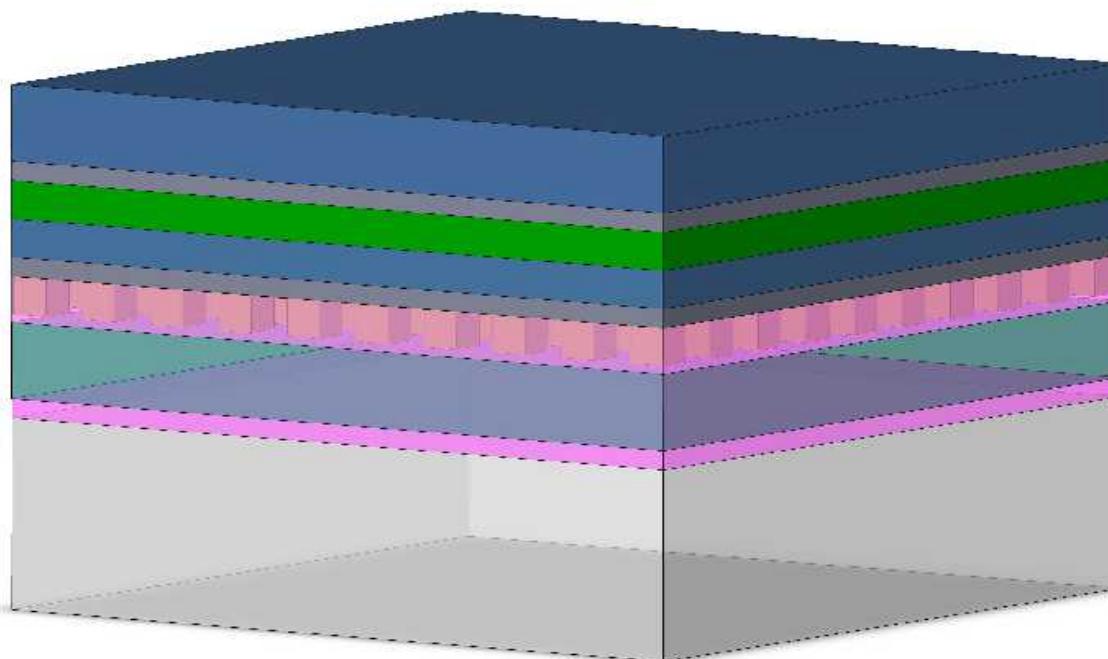
The GaSb substrate is then lapped and polished to 50mm thickness.



■	GaSb
■	InAsSb
■	AlGaAsSb
■	Au
□	Ti
■	Si <sub>3</sub> N <sub>4</sub>
■	BCB
■	c-Sapphire

# Fabrication Process Flow

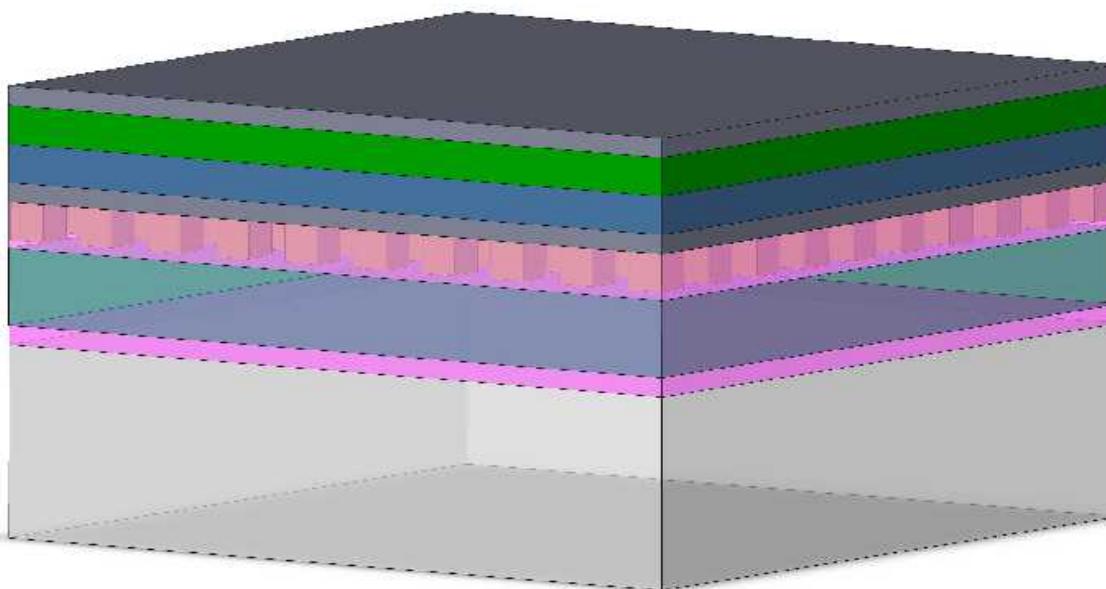
The remaining 50mm of GaSb substrate is chemically etched away in a solution of citric acid and chromium trioxide, with the etch stopping on InAsSb.



<span style="background-color: #666; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	GaSb
<span style="background-color: #005293; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	InAsSb
<span style="background-color: #008000; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	AlGaAsSb
<span style="background-color: #FFD700; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	Au
<span style="border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	Ti
<span style="background-color: #FF0000; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	Si <sub>3</sub> N <sub>4</sub>
<span style="background-color: #ADD8E6; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	BCB
<span style="background-color: #B0C4DE; border: 1px solid black; display: inline-block; width: 10px; height: 10px;"></span>	c-Sapphire

# Fabrication Process Flow

The InAsSb etch stop layer is selectively removed in a solution of citric acid and hydrogen peroxide, stopping on the p-type GaSb layer.

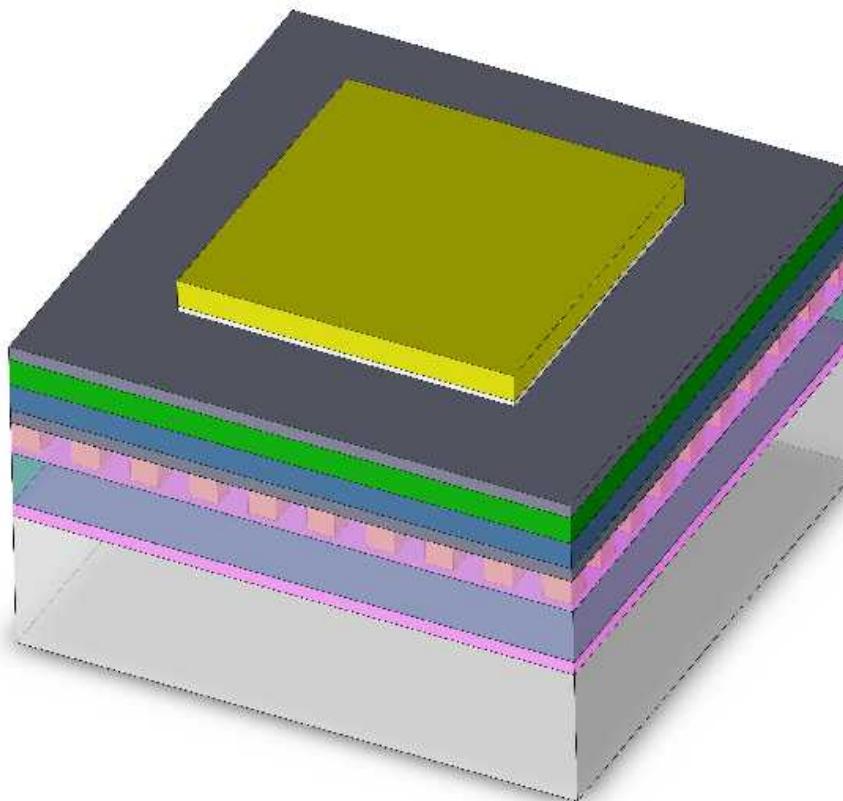


■	GaSb
■	InAsSb
■	AlGaAsSb
■	Au
□	Ti
■	Si <sub>3</sub> N <sub>4</sub>
■	BCB
■	c-Sapphire



# Fabrication Process Flow

The FPA pixel fabrication begins by defining a Ti/Au metal contact on the GaSb surface.



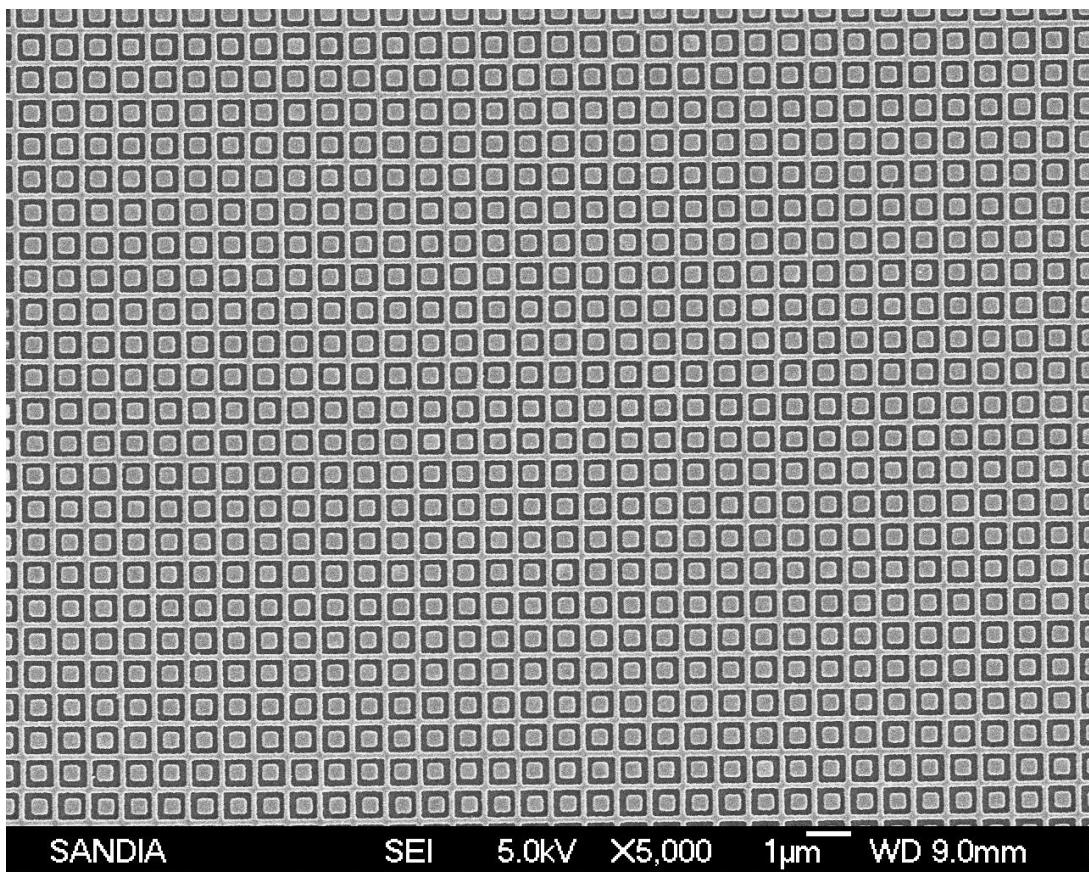
	GaSb
	InAsSb
	AlGaAsSb
	Au
	Ti
	Si <sub>3</sub> N <sub>4</sub>
	BCB
	c-Sapphire



# Fabricated Device

We have written  
nanoantenna patterns.

Substrate removal and  
epoxy underfill have proven  
to be difficult processes.

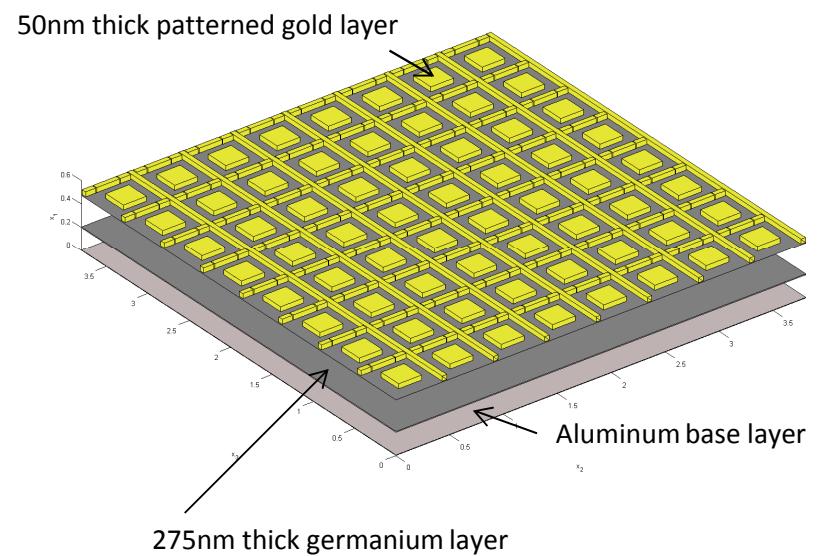
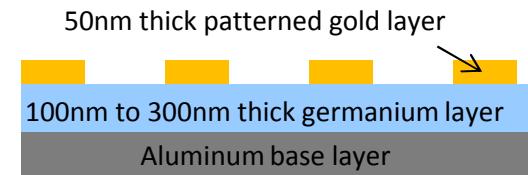
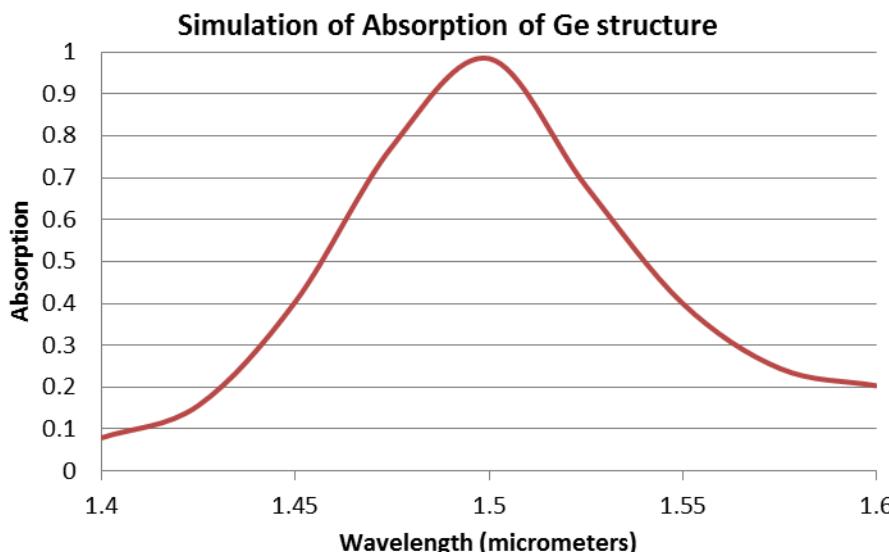


# Germanium Detector

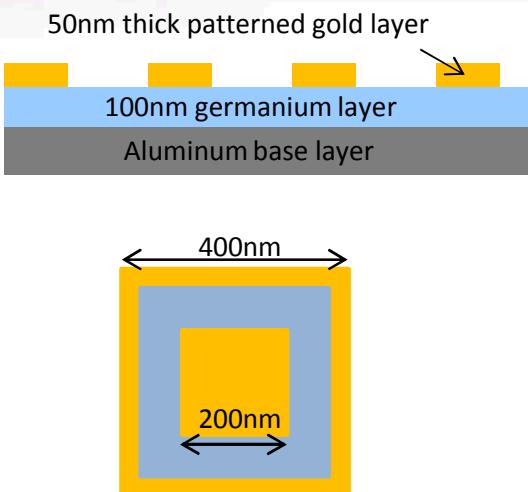
As with the other designs, this one involves a detection material between two metal layers. Since it is for the near-IR, the detector layer is quite thin. The metal top and bottom layers act as contacts.

As it is thin, it is very fast as carriers move to a metal electrode quickly. Since the metal wire grid is not a large solid piece of metal, the capacitance should also be low.

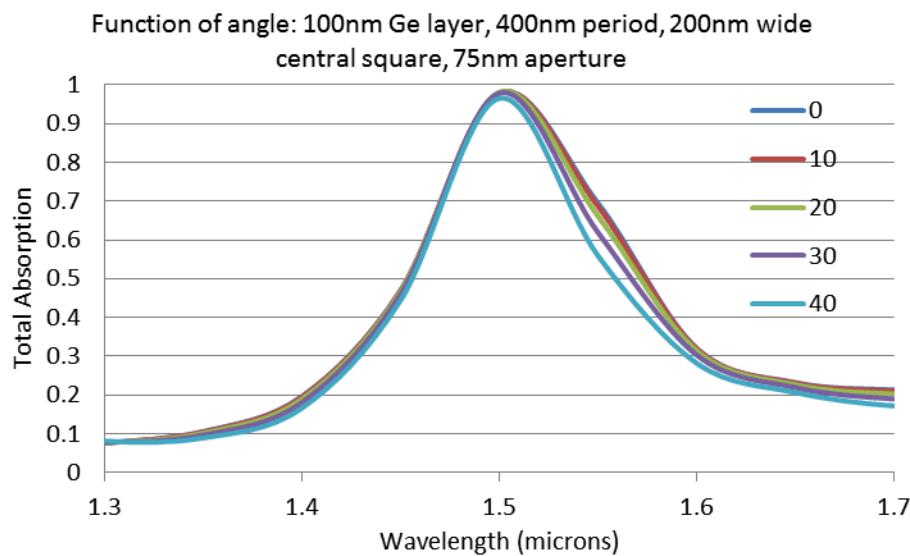
We designed and simulated a structure with dimensions below to work at  $1.5\mu\text{m}$ .



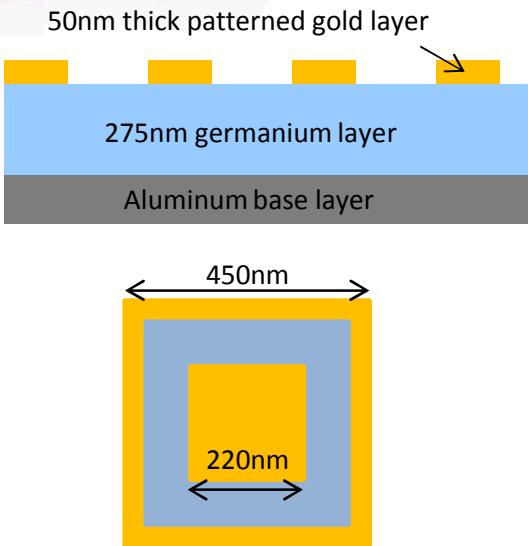
# Thin Version



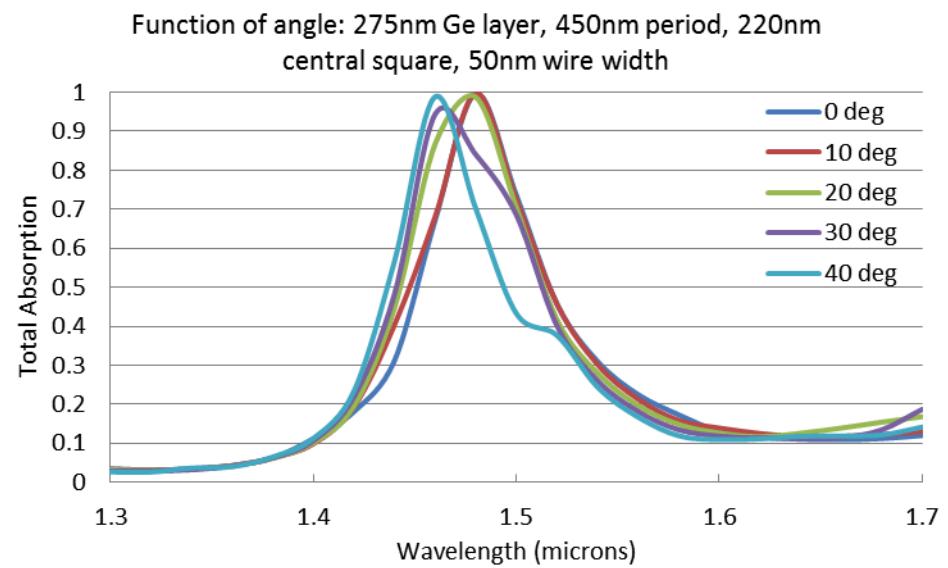
On this one I simulated a broader band (lower left), but the main feature is at lower right. There is virtually no change from normal out to 40deg. In any practical imaging system, this is more than enough.



# Thick Version

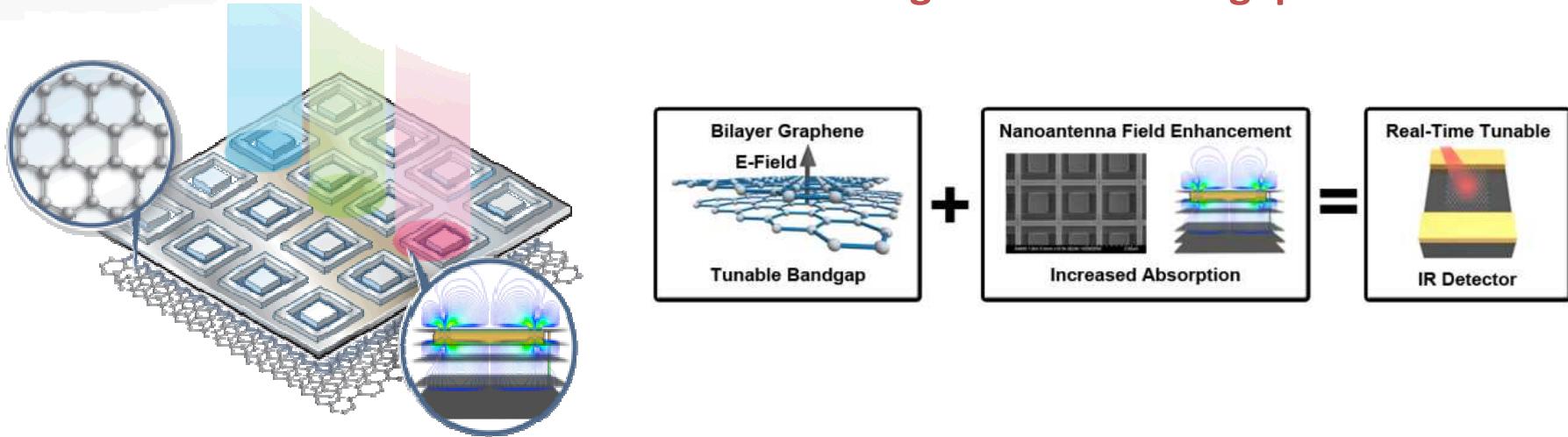


In this version we see a shift with angle of the peak and also a change in lineshape. I am not sure if there are two modes that are excited or what. Probably worth looking at the fields to see what the difference is.



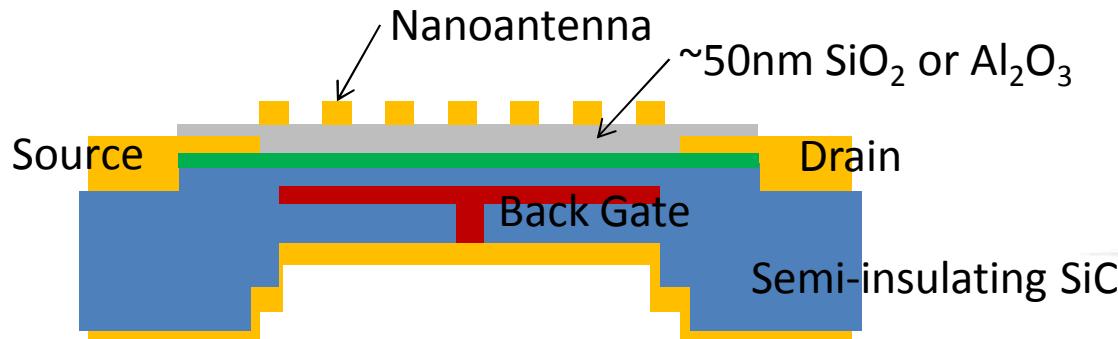
# Nanoantenna-Enabled Bilayer Graphene Detectors

IR detection with a real-time voltage-tunable bandgap.



The 2 atomic layers of bilayer graphene only absorb 4.6% of an incident plane wave.

We can concentrate the light with the nanoantenna for **10X** greater efficiency.





# Summary

**The nanoantenna concept allows for a new detector architecture for many IR detector platforms: irrespective of material.**

**Very thin active layer leads to**

- Less dark current
- Less crosstalk
- Faster operation

**The nanoantenna gives us**

- Spectral or polarization filtering by changing pattern from pixel to pixel
- Built-in wide-angle antireflection coating
- Built in EMI protection
- A material-agnostic device